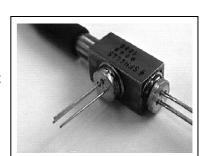
BIDI™ Transceiver Optical Module for ATM-PON ONU Applications, 1300 nm Emitting-/1550 nm Receiving Function, High Power FP-Laser, InGaAs/InP-PIN Photodiode

- Designed for applications in passive-optical networks according FSAN, ITU-G.983
- Suitable for ONU applications, 155 Mbit/s and 622 Mbit/s downstream bitrate, Class B and Class C
- Uncooled 1300 nm FP Laser Diode with Multi-Quantum Well structure
- Ternary Moniordiode at rear laser mirror for monitoring and control of radiant power
- Integrated Wavelength Division Multiplexer
- InGaAs/InP-PIN-photodiode with 1300 nm blocking filter
- Hermetically sealed subcomponents, similar to TO 18
- With singlemode fiber pigtail



Maximum Ratings

Output power ratings refer to the optical port. The operating temperature of the submount is identical to the case temperature

Module	Symbol	Value	Unit
Operating temperature range at case	T_{C}	- 40 + 85	°C
Storage temperature range	T_{stg}	- 40 + 85	°C
Soldering temperature $t_{\text{max}} = 10 \text{ s}$, 2 mm distance from bottom edge of case	$T_{\mathbb{S}}$	260	°C

Laser Diode	Symbol	Value	Unit
Direct forward current	I _{F max}	120	mA
Radiant power CW	Popt max	4	mW
Reverse Voltage	$V_{R\;max}$	2	V

Monitor Diode	Symbol	Value	Unit
Reverse Voltage	$V_{R\;max}$	10	V
Forward Current	I _{F max}	2	mA

PIN Photodiode	Symbol	Value	Unit
Forward current	$I_{F\;max}$	2	mA
Reverse voltage	V_{R}	10	V
Maximum optical power into the optical port	P _{port max}	3	mW

Characteristics:

All optical data refer to the optical port at – 40 to + 85 °C Package-Temperature.

Laser Diode	Symbol	Min	Max	Unit
Optical output power (average)	Popt av	1	_	mW
Optical output power (peak)	Popt peak	2	_	mW
Emission wavelength center of range $(P_{\text{opt}} = 1 \text{ mW})$	λ	1260	1360	nm
Spectral Width (RMS, $P_{\text{opt}} = 1 \text{ mW}$)	Δλ	_	5.8	nm
Threshold current	I_{th}	2	45	mA
Forward voltage ($P_{\text{opt}} = 1 \text{ mW}$)	V_{F}	_	1.5	V
Radiant power at I _{th}	P_{th}	_	50	μW
Slope efficiency	S	35	150	mW/A
Variation of 1st derivative of P/I (0.1 to 2.0 mW)	dP/dI	- 30	30	%
Differential series resistance ($P_{opt} = 1 \text{ mW}$)	rs	_	8	Ω
Rise and fall time (10% - 90%)	$t_{\rm r},\ t_{\rm f}$	_	0.5	ns
Temperature coefficient of wavelength	TC_{λ}	_	0.5	nm/K

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Monitor-Diode	Symbol	Min	Max	Unit
Dark current, $V_R = 5 \text{ V}$, $P_{\text{opt}} = 0$	I_{R}	_	0.5	μA
Photocurrent, $P_{opt} = 1 \text{ mW}$	I_{P}	100	1000	μΑ
Capacitance, V_R = 5V, f =1MHz	C_5	_	10	pF
Tracking error, V_R = 5V, (see note 1)	TE	-1	1	dB

Receiver-Diode	Symbol	Min	Max	Unit
Spectral sensitivity $\lambda = 1550 \text{ nm}, V_R = 5 \text{ V}$	$S_{\lambda 1550}$	0.65	1.0	A/W
Rise and fall time (10% - 90%) $R_{\rm L}$ = 50 Ω , $V_{\rm R}$ = 5 V, λ = 1310nm, $P_{\rm opt}$ = 100 μ W	$t_{\rm r}; t_{\rm f}$	_	0.5	ns
Total capacitance $V_{\rm R}$ = 5 V, f = 1 MHz	C_2	_	1.5	pF
Dark current $V_{R} = 5 \text{ V}, P_{\text{opt}} = 0$	I_{D}	_	50	nA

Module	Symbol	Value	Unit
Optical Crosstalk (see note 2)	CRT	< - 47	dB
Backreflection (Return Loss) @ λ _{in} =1310nm	_	< - 6	dB
Backreflection (Return Loss) @ λ _{in} =1550nm	_	< - 20	dB

Note 1: The tracking error TE is the variation rate of $P_{\rm opt}$ at constant current $I_{\rm mon}$ over a specified temperature range and relative to the reference point: $I_{\rm mon,ref} = I_{\rm mon}$ (T = 25 °C, $P_{\rm opt} = 1$ mW). Thus, TE is given by:

$$TE[dB] = 10 \times \log \frac{P_{opt}[T_c] - P_{opt}[25^{\circ}C]}{P_{opt}[25^{\circ}C]}$$

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Note 2: Optical Crosstalk is defined as $CRT = 10 \times log(P_2/P_1)$ with: $P_1 = P_{opt} = 1 \text{ mW}$ with no optical input power P_{port} and P_2 the necessary optical input power

Pport at $\lambda = 1550$ nm to get for $P_{\text{opt}} = 0$ the same receiver signal level as

before (VR = 2 V).

Accompanying Information

T = 25 °C: Threshold current, slope eficiency, monitor current for 1 mW output power,

peak wavelength for 1 mW output power.

T = 85 °C: Threshold current, slope efficiency

Pigtail

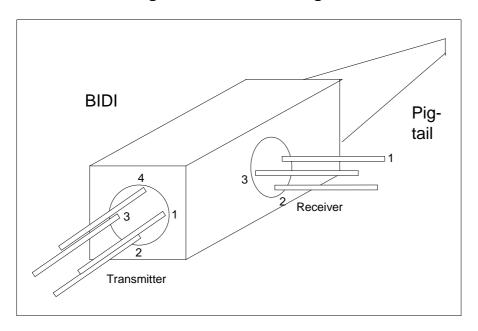
Fiber Pigtail, Single Mode, Silica	Min	Max	Unit
Mode field diameter	8	10	μm
Cladding diameter	123	127	μm
Mode field/cladding concentricity error	_	1	μm
Cladding non-circularity	_	2	%
Mode field non-circularity	_	6	%
Cut-off wavelength	1250	_	nm
Jacket diameter	8.0	1.0	mm
Bending radius	30	-	mm
Tensile strength fiber/case	5	_	N
Length	0.8	1.2	m

Connector

all standard connectors like FC/PC, SC, SC APC, available

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Schematic Package Outline and Pinning



Transmitter

1 LK

2 Case

3 MK, LA

4 MA

Receiver

1 Photodiode K

2 Gnd, Case

3 Photodiode A